

IGBT SIP Module (Short Circuit Rated Ultrafast IGBT)



IMS-2

PRODUCT SUMMARY

OUTPUT CURRENT IN A TYPICAL 20 kHz MOTOR DRIVE

I_{RMS} per phase (1.94 kW total) with $T_C = 90^\circ\text{C}$	6.7 A _{RMS}
T_J	125 °C
Supply voltage	360 Vdc
Power factor	0.8
Modulation depth (see fig. 1)	115 %
$V_{CE(on)}$ (typical) at $I_C = 6.0\text{ A}$, 25 °C	1.72 V

FEATURES

- Short circuit rated ultrafast: Optimized for high speed over 5.0 kHz (see fig. 1 for current vs. frequency curve), and short circuit rated to 10 μs at 125 °C, $V_{GE} = 15\text{ V}$
- Fully isolated printed circuit board mount package
- Switching-loss rating includes all "tail" losses
- HEXFRED® soft ultrafast diodes
- Totally lead (Pb)-free
- Designed and qualified for industrial level



RoHS
COMPLIANT

DESCRIPTION

The IGBT technology is the key to Vishay's HPP advanced line of IMS (Insulated Metal Substrate) power modules. These modules are more efficient than comparable bipolar transistor modules, while at the same time having the simpler gate-drive requirements of the familiar power MOSFET. This superior technology has now been coupled to a state of the art materials system that maximizes power throughput with low thermal resistance. This package is highly suited to motor drive applications and where space is at a premium.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		600	V
Continuous collector current, each IGBT	I_C	$T_C = 25^\circ\text{C}$	11	A
		$T_C = 100^\circ\text{C}$	6.0	
Pulsed collector current	I_{CM}	Repetitive rating; $V_{GE} = 20\text{ V}$, pulse width limited by maximum junction temperature See fig. 20	22	A
Clamped inductive load current	I_{LM}	$V_{CC} = 80\% (V_{CES})$, $V_{GE} = 20\text{ V}$, $L = 10\text{ }\mu\text{H}$, $R_G = 22\text{ }\Omega$ See fig. 19	22	A
Diode continuous forward current	I_F	$T_C = 100^\circ\text{C}$	6.1	A
Diode maximum forward current	I_{FM}		22	A
Short circuit withstand time	t_{SC}		10	μs
Gate to emitter voltage	V_{GE}		± 20	V
Isolation voltage	V_{ISOL}	Any terminal to case, $t = 1\text{ minute}$	2500	V_{RMS}
Maximum power dissipation, each IGBT	P_D	$T_C = 25^\circ\text{C}$	36	W
		$T_C = 100^\circ\text{C}$	14	
Operating junction and storage temperature range	T_J, T_{Stg}		- 40 to + 150	°C
Soldering temperature		For 10 s, (0.063" (1.6 mm) from case)	300	
Mounting torque		6-32 or M3 screw	5 to 7 (0.55 to 0.8)	lbf · in (N · m)

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TYP.	MAX.	UNITS
Junction to case, each IGBT, one IGBT in conduction	R_{thJC} (IGBT)	-	3.5	°C/W
Junction to case, each DIODE, one DIODE in conduction	R_{thJC} (DIODE)	-	5.5	
Case to sink, flat, greased surface	R_{thCS} (MODULE)	0.10	-	
Weight of module		20	-	g
		0.7	-	oz.

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	V _{(BR)CES} ⁽¹⁾	V _{GE} = 0 V, I _C = 250 μA		600	-	-	V
Temperature coeff. of breakdown voltage	ΔV _{(BR)CES} /ΔT _J	V _{GE} = 0 V, I _C = 1.0 mA		-	0.45	-	V/°C
Collector to emitter saturation voltage	V _{CE(on)}	I _C = 6.0 A	V _{GE} = 15 V See fig. 2, 5	-	1.72	2.10	V
		I _C = 11 A		-	2.00	-	
		I _C = 6.0 A, T _J = 150 °C		-	1.60	-	
Gate threshold voltage	V _{GE(th)}	V _{CE} = V _{GE} , I _C = 250 μA		3.0	-	6.0	mV/°C
Temperature coeff. of threshold voltage	ΔV _{GE(th)} /ΔT _J			-	- 13	-	
Forward transconductance	g _{fe} ⁽²⁾	V _{CE} = 100 V, I _C = 12 A		3.0	6.0	-	S
Zero gate voltage collector current	I _{CES}	V _{GE} = 0 V, V _{CE} = 600 V		-	-	250	μA
		V _{GE} = 0 V, V _{CE} = 600 V, T _J = 150 °C		-	-	2500	
Diode forward voltage drop	V _{FM}	I _C = 12 A	See fig. 13	-	1.4	1.7	V
		I _C = 12 A, T _J = 150 °C		-	1.3	1.6	
Gate to emitter leakage current	I _{GES}	V _{GE} = ± 20 V		-	-	± 100	nA

Notes(1) Pulse width $\leq 80\text{ }\mu\text{s}$, duty factor $\leq 0.1\%$ (2) Pulse width $5.0\text{ }\mu\text{s}$; single shot

SWITCHING CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Total gate charge (turn-on)	Q _g	I _C = 6 A V _{CC} = 400 V See fig. 8		-	61	91	nC	
Gate to emitter charge (turn-on)	Q _{ge}			-	7.4	11		
Gate to collector charge (turn-on)	Q _{gc}			-	27	40		
Turn-on delay time	t _{d(on)}	T _J = 25 °C I _C = 6.0 A, V _{CC} = 480 V V _{GE} = 15 V, R _G = 23 Ω Energy losses include “tail” and diode reverse recovery See fig. 9, 10, 18		-	55	-	ns	
Rise time	t _r			-	24	-		
Turn-off delay time	t _{d(off)}			-	107	160		
Fall time	t _f			-	92	140		
Turn-on switching loss	E _{on}			-	0.28	-	mJ	
Turn-off switching loss	E _{off}			-	0.10	-		
Total switching loss	E _{ts}			-	0.39	0.50		
Short circuit withstand time	t _{sc}	V _{CC} = 360 V, T _J = 125 °C V _{GE} = 15 V, R _G = 23 Ω, V _{CPK} < 500 V		10	-	-	μs	
Turn-on delay time	t _{d(on)}	T _J = 150 °C I _C = 6.0 A, V _{CC} = 480 V V _{GE} = 15 V, R _G = 23 Ω Energy losses include “tail” and diode reverse recovery See fig. 10, 11, 18		-	54	-	ns	
Rise time	t _r			-	24	-		
Turn-off delay time	t _{d(off)}			-	161	-		
Fall time	t _f			-	244	-		
Total switching loss	E _{ts}			-	0.60	-	mJ	
Input capacitance	C _{ies}	V _{GE} = 0 V	See fig. 7	-	740	-	pF	
Output capacitance	C _{oes}	V _{CC} = 30 V		-	100	-		
Reverse transfer capacitance	C _{res}	f = 1.0 MHz		-	9.3	-		
Diode reverse recovery time	t _{rr}	T _J = 25 °C	See fig. 14	I _F = 12 A V _R = 200 V dI/dt = 200 A/μs	-	42	60	ns
		T _J = 125 °C			-	80	120	
Diode peak reverse recovery current	I _{rr}	T _J = 25 °C	See fig. 15		-	3.5	6.0	A
		T _J = 125 °C			-	5.6	10	
Diode reverse recovery charge	Q _{rr}	T _J = 25 °C	See fig. 16		-	80	180	nC
		T _J = 125 °C			-	220	600	
Diode peak rate of fall of recovery during t _b	dI _(rec) M/dt	T _J = 25 °C	See fig. 17		-	180	-	A/μs
		T _J = 125 °C			-	120	-	

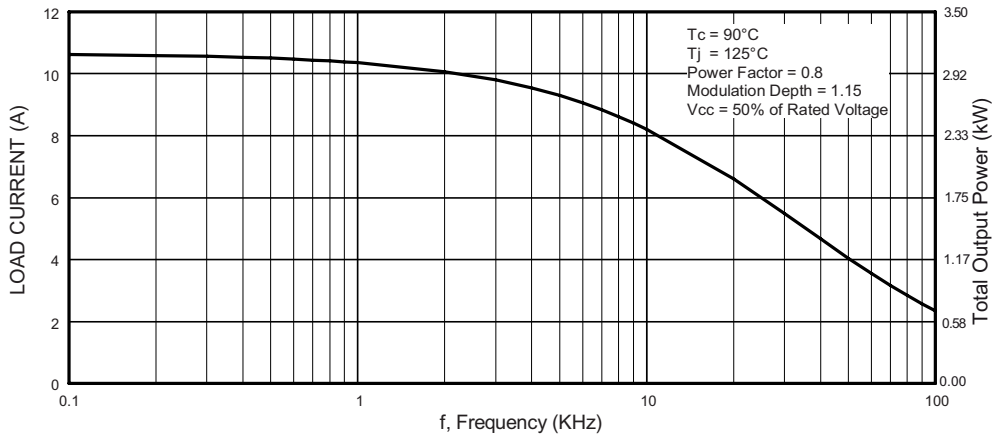


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of Fundamental)

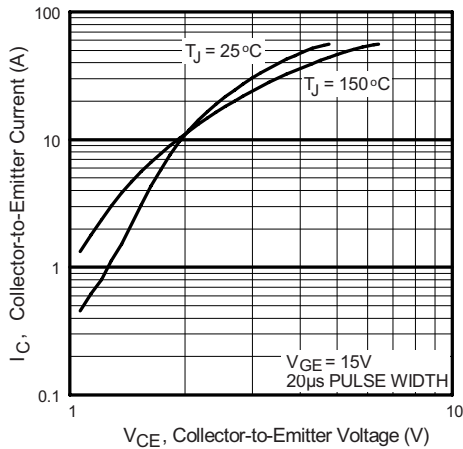


Fig. 2 - Typical Output Characteristics

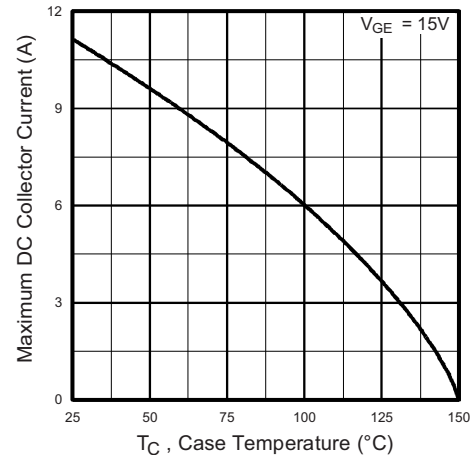


Fig. 4 - Maximum Collector Current vs. Case Temperature

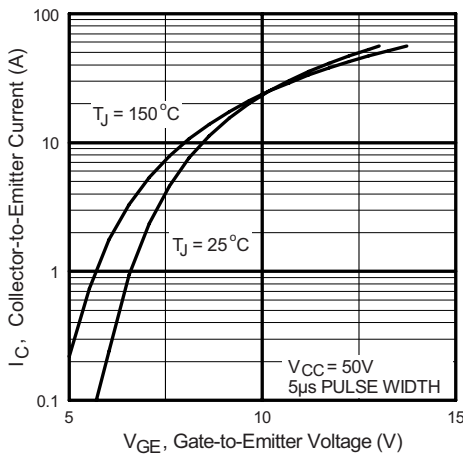


Fig. 3 - Typical Transfer Characteristics

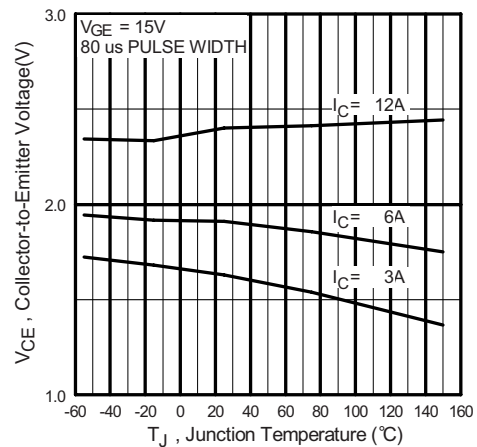


Fig. 5 - Typical Collector to Emitter Voltage vs.
Junction Temperature

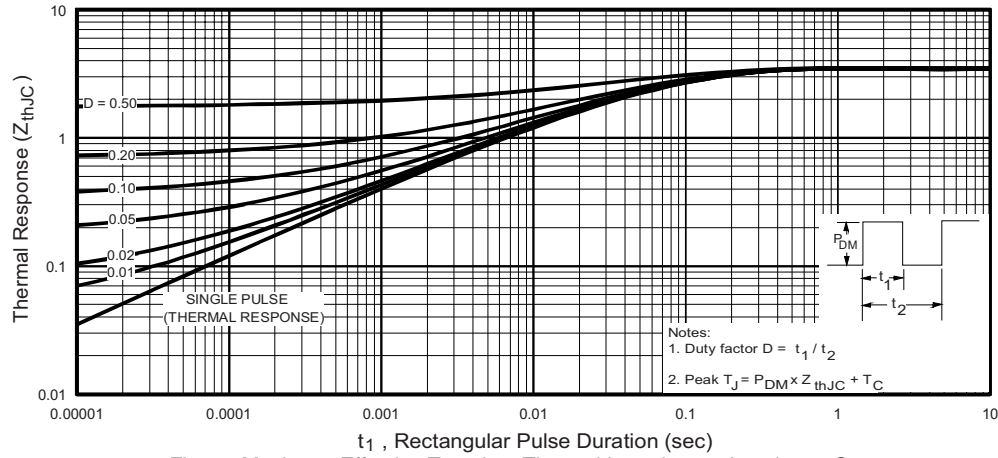


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction to Case

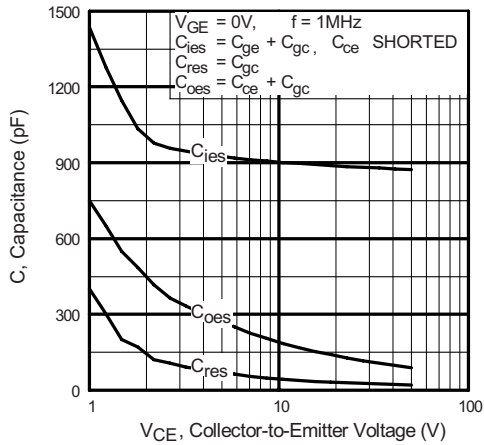


Fig. 7 - Typical Capacitance vs. Collector to Emitter Voltage

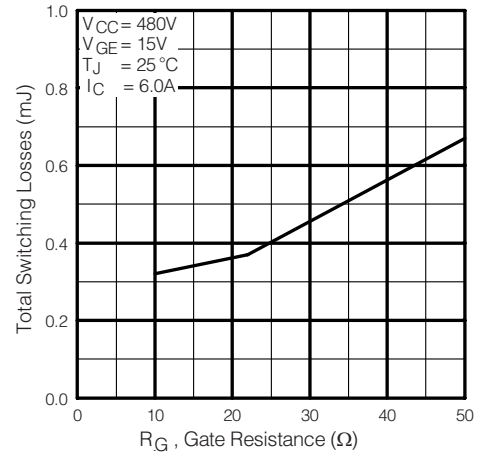


Fig. 9 - Typical Switching Losses vs. Gate Resistance

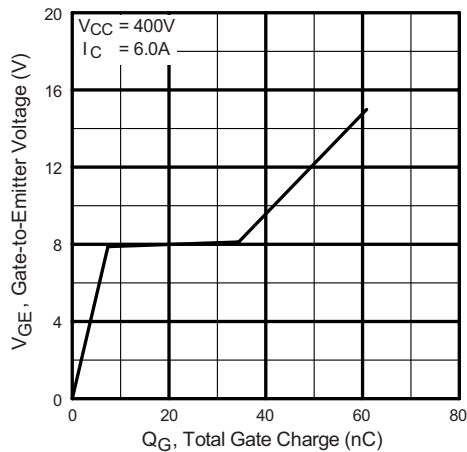


Fig. 8 - Typical Gate Charge vs. Gate to Emitter Voltage

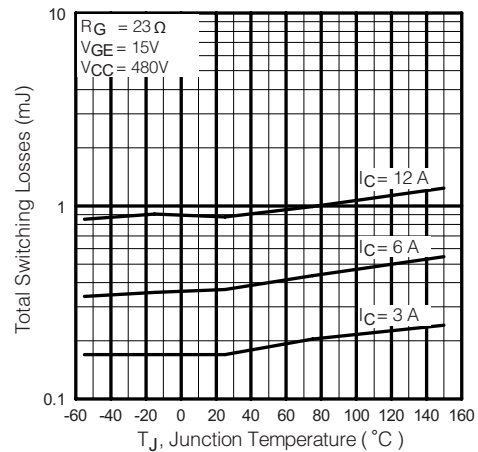
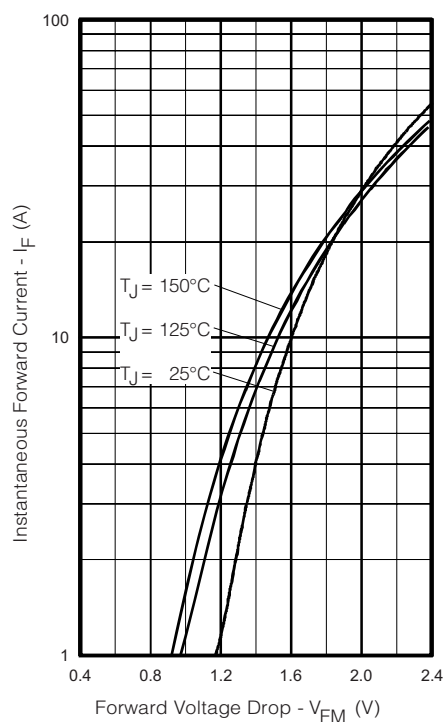
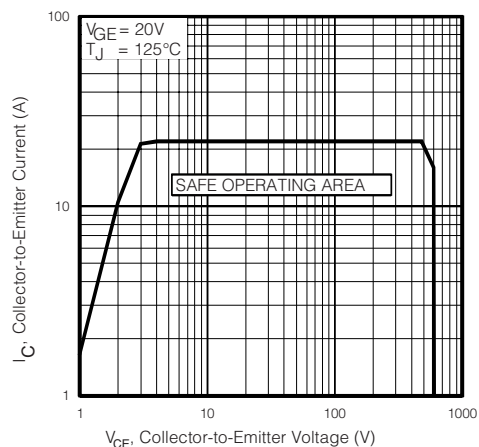
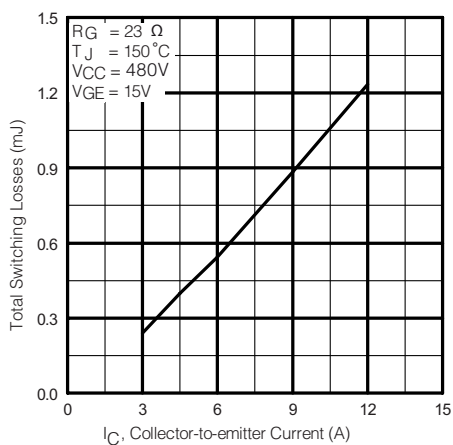


Fig. 10 - Typical Switching Losses vs. Junction Temperature



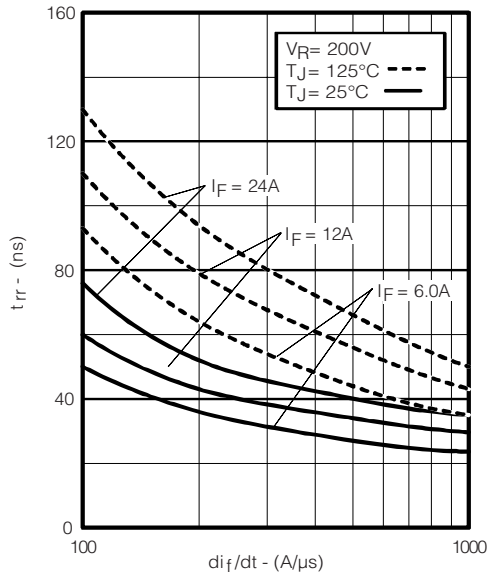


Fig. 14 - Typical Reverse Recovery Time vs. di_F/dt

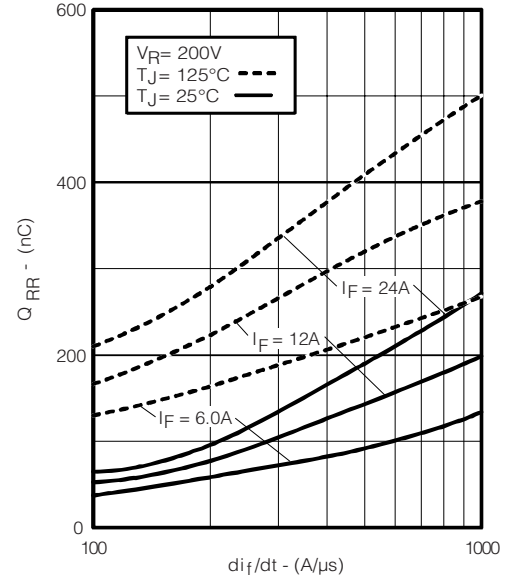


Fig. 16 - Typical Stored Charge vs. di_F/dt

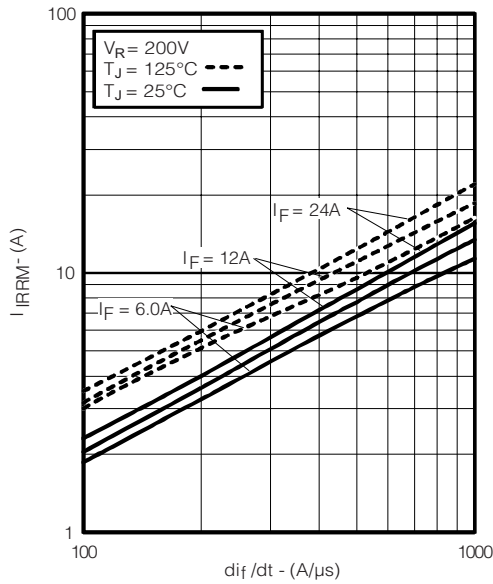


Fig. 15 - Typical Recovery Current vs. di_F/dt

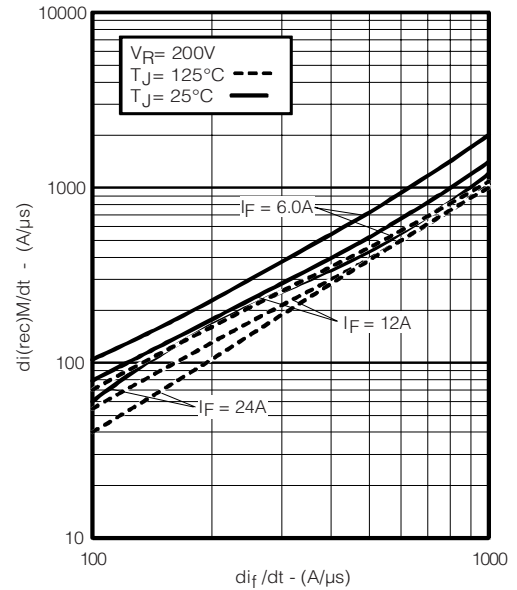


Fig. 17 - Typical $dI_{(rec)M}/dt$ vs di_F/dt

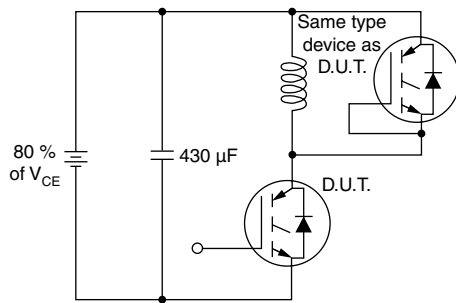


Fig. 18a - Test Circuit for Measurements of I_{LM} , E_{on} , $E_{off(diode)}$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

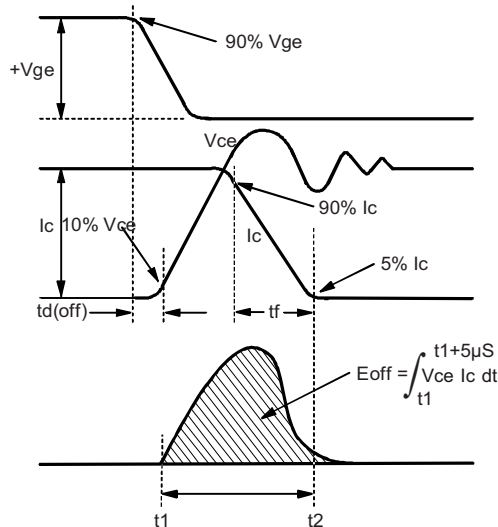


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

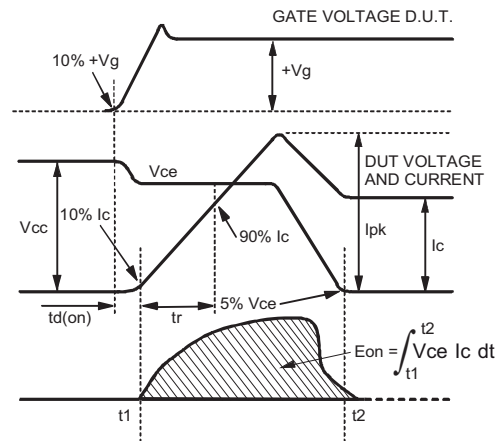


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

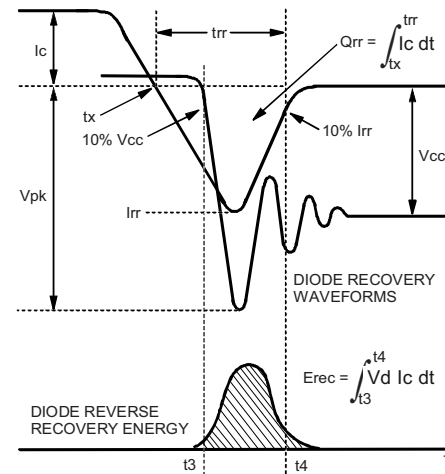


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

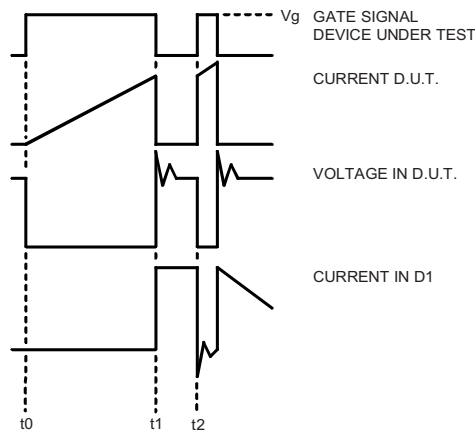


Fig. 18e - Macro Waveforms for Figure 18a's Test Circuit

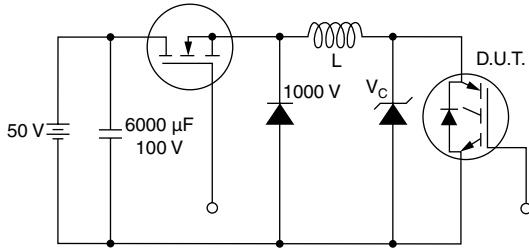


Fig. 19 - Clamped Inductive Load Test Circuit

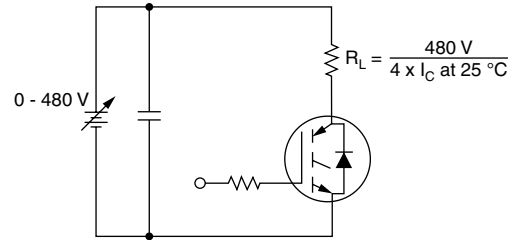
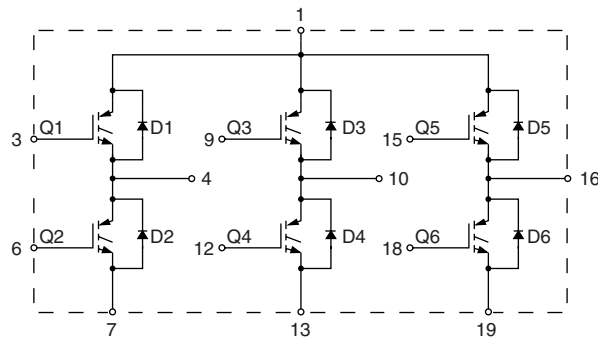


Fig. 20 - Pulsed Collector Current Test Circuit

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95066

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